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ON Semiconductor®

FQB7N60 / FQI7N60

N-Channel QFET® MOSFET

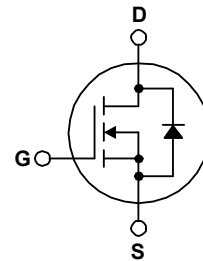
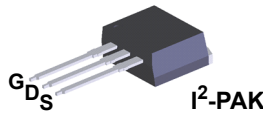
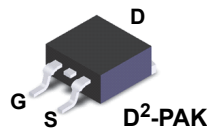
600 V, 7.4 A, 1.0 Ω

Description

This N-Channel enhancement mode power MOSFET is produced using ON Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 7.4 A, 600 V, $R_{DS(on)} = 1.0 \Omega$ (Max.) @ $V_{GS} = 10 \text{ V}$, $I_D = 3.7 \text{ A}$
- Low Gate Charge (Typ. 29 nC)
- Low C_{rss} (Typ. 16 pF)
- 100% Avalanche Tested



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FQB7N60TM FQB7N60TM-WS FQI7N60TU	Unit
V_{DSS}	Drain-Source Voltage	600	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$)	7.4	A
		4.7	A
I_{DM}	Drain Current - Pulsed (Note 1)	29.6	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	580	mJ
I_{AR}	Avalanche Current (Note 1)	7.4	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	14.2	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$) *	3.13	W
	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	142	W
		1.14	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FQB7N60TM FQB7N60TM-WS FQI7N60TU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.88	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	
	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	40	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQB7N60TM	FQB7N60	D ² -PAK	Tape and Reel	330 mm	24 mm	800 units
FQB7N60TM-WS	FQB7N60S	D ² -PAK	Tape and Reel	330 mm	24 mm	800 units
FQI7N60TU	FQI7N60	I ² -PAK	Tube	N/A	N/A	50 units

Electrical Characteristics T_c = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	600	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	--	0.67	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600 V, V _{GS} = 0 V	--	--	10	μA
		V _{DS} = 480 V, T _C = 125°C	--	--	100	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	3.0	--	5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 3.7 A	--	0.8	1.0	Ω
g _{FS}	Forward Transconductance	V _{DS} = 50 V, I _D = 3.7 A	--	6.4	--	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	1100	1430	pF
C _{oss}	Output Capacitance		--	135	175	pF
C _{rss}	Reverse Transfer Capacitance		--	16	21	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time	V _{DD} = 300 V, I _D = 7.4 A, R _G = 25 Ω	--	30	70	ns	
t _r	Turn-On Rise Time		--	80	170	ns	
t _{d(off)}	Turn-Off Delay Time		(Note 4)	--	65	140	ns
t _f	Turn-Off Fall Time		(Note 4)	--	60	130	ns
Q _g	Total Gate Charge	V _{DS} = 480 V, I _D = 7.4 A, V _{GS} = 10 V	--	29	38	nC	
Q _{gs}	Gate-Source Charge		(Note 4)	--	7	--	nC
Q _{gd}	Gate-Drain Charge		(Note 4)	--	14.5	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current	--	--	7.4	A	
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	29.6	A	
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 7.4 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 7.4 A, di _F / dt = 100 A/μs	--	320	--	ns
Q _{rr}	Reverse Recovery Charge		--	2.4	--	μC

Notes:

1. Repetitive rating : pulse-width limited by maximum junction temperature.
2. L = 19.5 mH, I_{AS} = 7.4 A, V_{DD} = 50 V, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 7.4 A, di/dt ≤ 200 A/μs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C.
4. Essentially independent of operating temperature.

Typical Characteristics

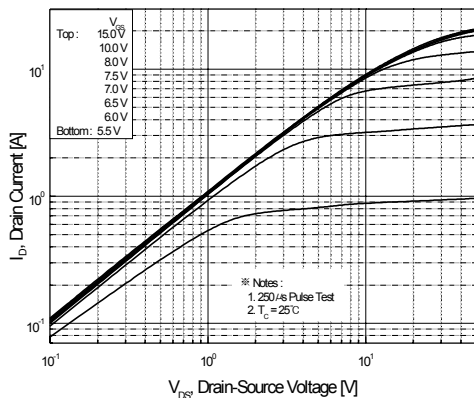


Figure 1. On-Region Characteristics

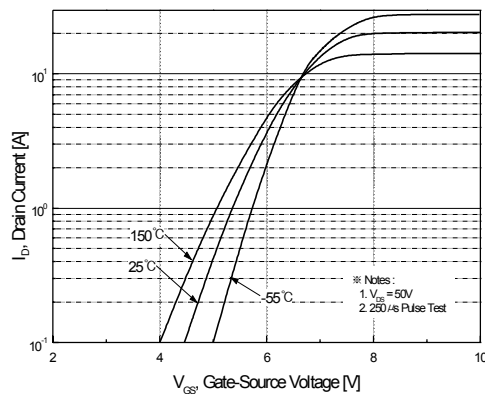


Figure 2. Transfer Characteristics

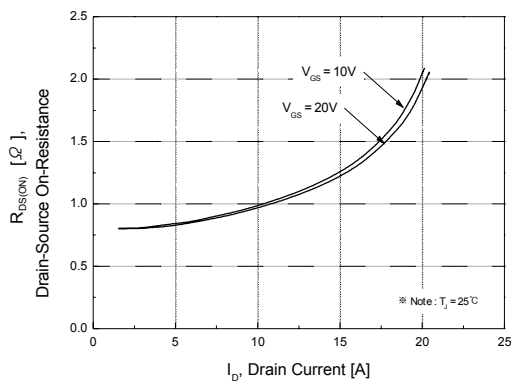


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

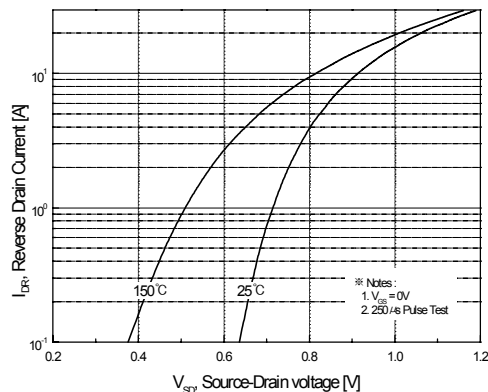


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

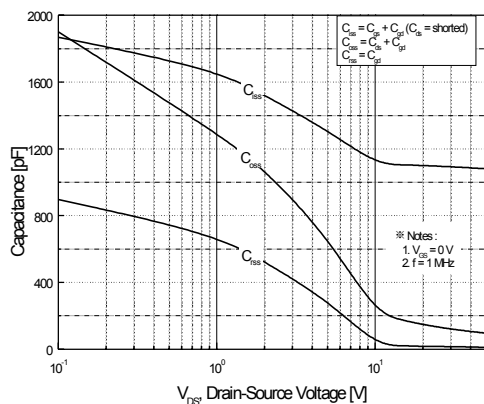


Figure 5. Capacitance Characteristics

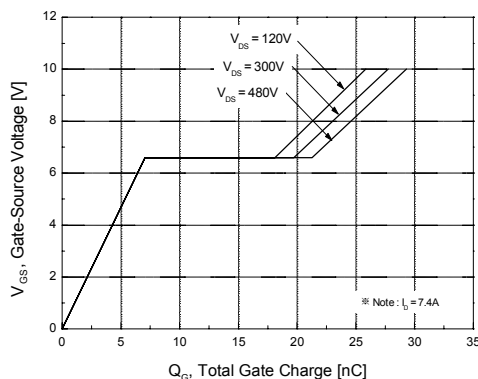


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

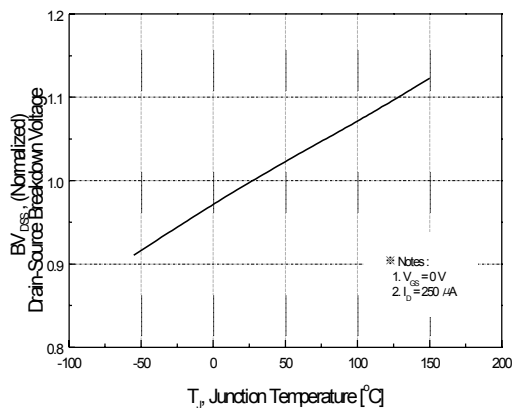


Figure 7. Breakdown Voltage Variation vs. Temperature

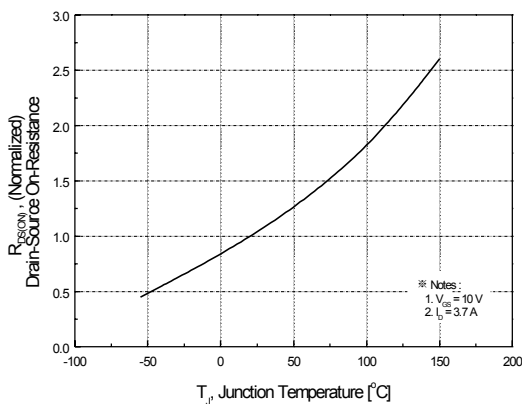


Figure 8. On-Resistance Variation vs. Temperature

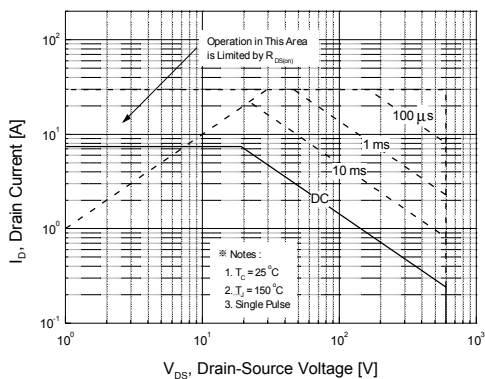


Figure 9. Maximum Safe Operating Area

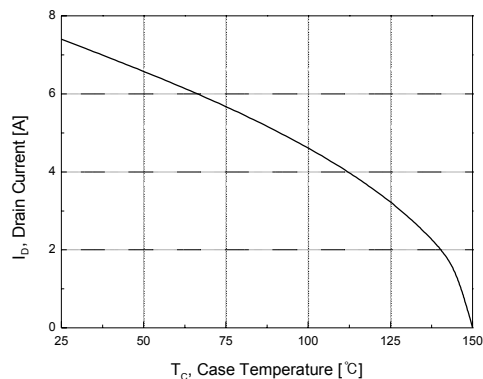


Figure 10. Maximum Drain Current vs. Case Temperature

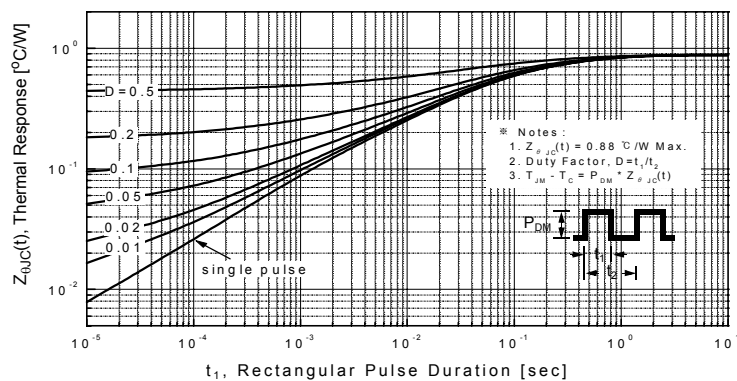


Figure 11. Transient Thermal Response Curve

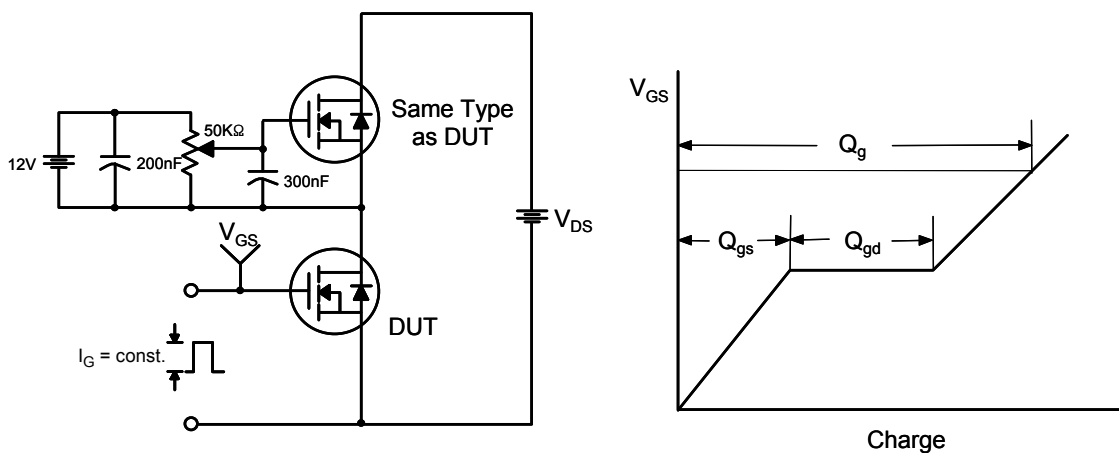


Figure 12. Gate Charge Test Circuit & Waveform

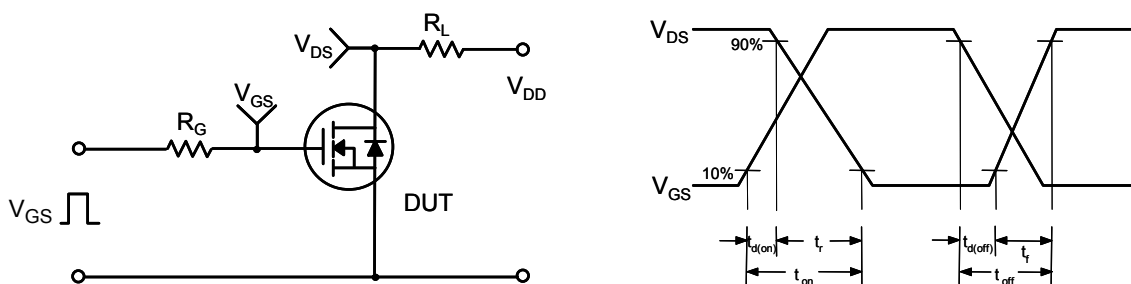


Figure 13. Resistive Switching Test Circuit & Waveforms

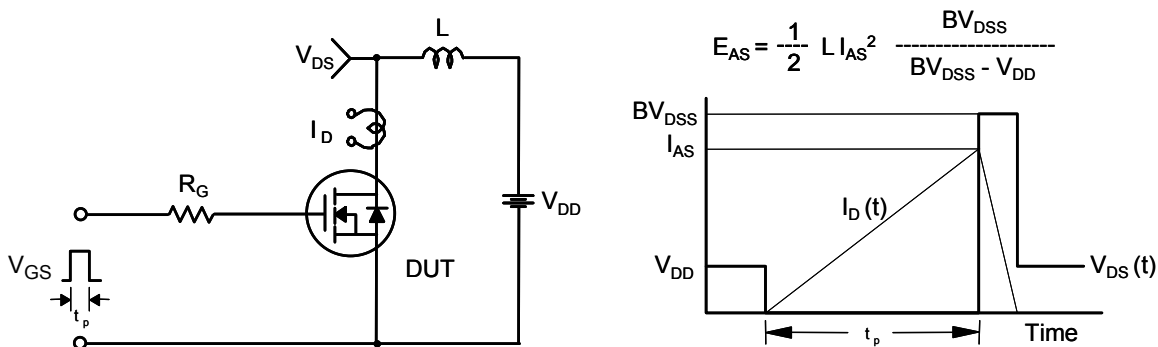


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

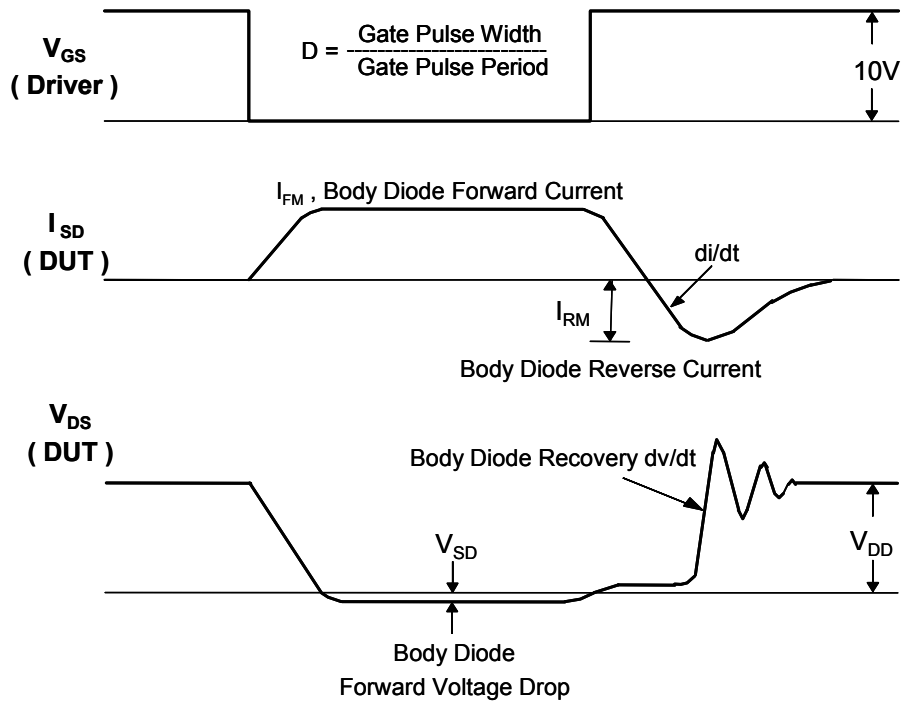
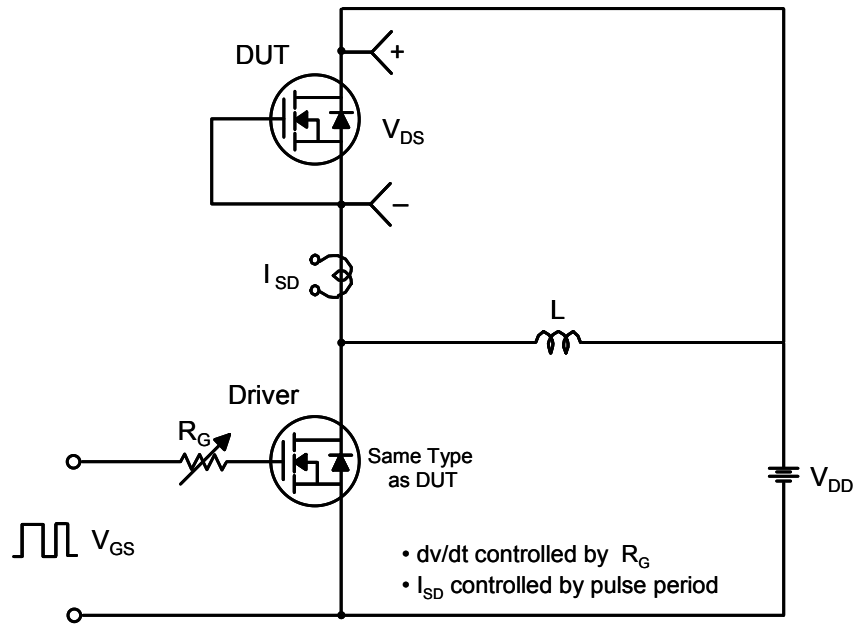


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

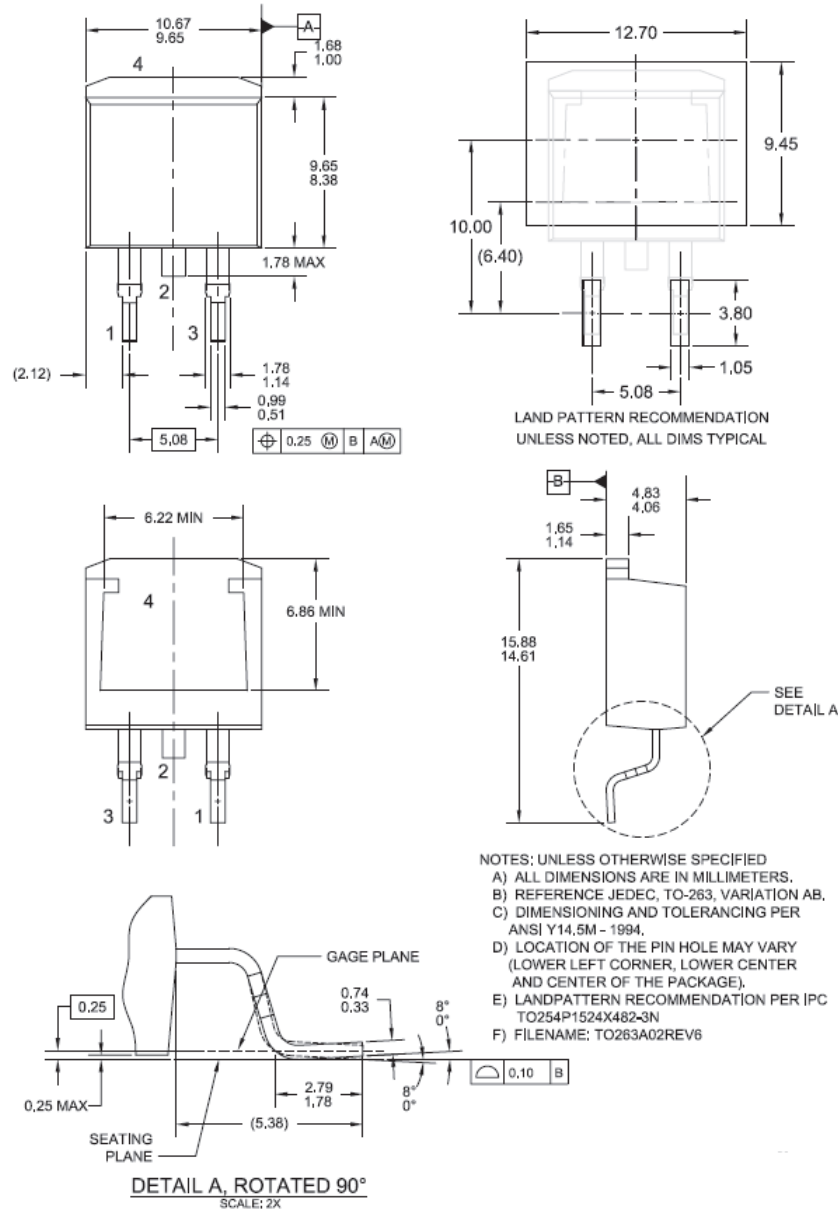
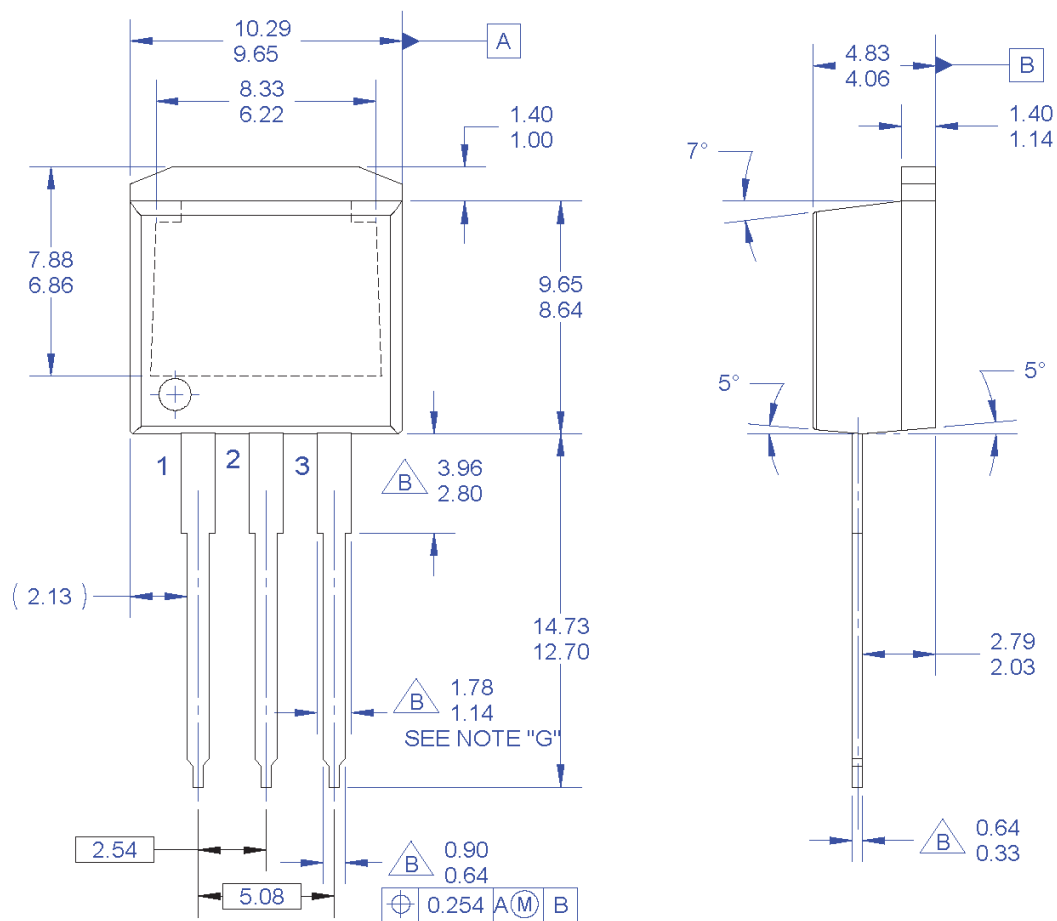


Figure 16. TO263 (D²PAK), Molded, 2-Lead, Surface Mount

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Mechanical Dimensions



NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO TO262 JEDEC VARIATION AA.
- △ B. DOES NOT COMPLY JEDEC STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ANSI Y14.5-1994.
- F. LOCATION OF PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF PACKAGE)
- G. MAXIMUM WIDTH FOR F102 DEVICE = 1.35 MAX.
- H. DRAWING FILE NAME: TO262A03REV5

Figure 17. TO262 (I²PAK), Molded, 3-Lead, Jedec Variation AA

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